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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, FlexRay, LINbus, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	68
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	40K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 30x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5604pef0mll6

1 Introduction

1.1 Document overview

This document provides electrical specifications, pin assignments, and package diagrams for the MPC5603P/4P series of microcontroller units (MCUs). It also describes the device features and highlights important electrical and physical characteristics. For functional characteristics, refer to the device reference manual.

1.2 Description

This 32-bit system-on-chip (SoC) automotive microcontroller family is the latest achievement in integrated automotive application controllers. It belongs to an expanding range of automotive-focused products designed to address chassis applications—specifically, electrical hydraulic power steering (EHPS) and electric power steering (EPS)—as well as airbag applications.

This family is one of a series of next-generation integrated automotive microcontrollers based on the Power Architecture technology.

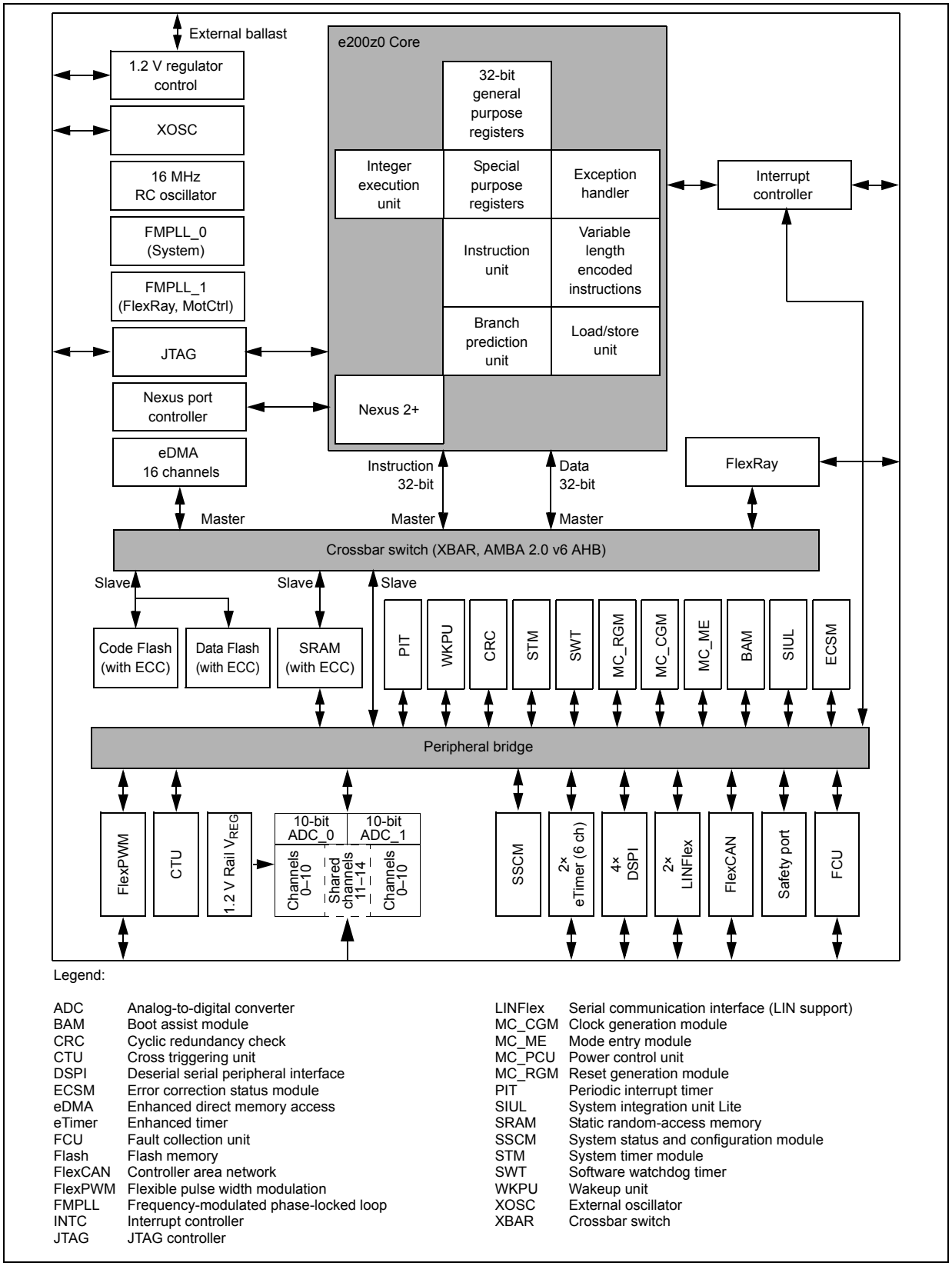
The advanced and cost-efficient host processor core of this automotive controller family complies with the Power Architecture embedded category. It operates at speeds of up to 64 MHz and offers high performance processing optimized for low power consumption. It capitalizes on the available development infrastructure of current Power Architecture devices and is supported with software drivers, operating systems and configuration code to assist with users implementations.

1.3 Device comparison

Table 1 provides a summary of different members of the MPC5604P family and their features to enable a comparison among the family members and an understanding of the range of functionality offered within this family.

Table 1. MPC5604P device comparison

Feature	MPC5603P	MPC5604P
Code flash memory (with ECC)	384 KB	512 KB
Data flash memory / EE option (with ECC)	64 KB (optional feature)	
SRAM (with ECC)	36 KB	40 KB
Processor core	32-bit e200z0h	
Instruction set	VLE (variable length encoding)	
CPU performance	0–64 MHz	
FMPLL (frequency-modulated phase-locked loop) module	2	
INTC (interrupt controller) channels	147	
PIT (periodic interrupt timer)	1 (includes four 32-bit timers)	
eDMA (enhanced direct memory access) channels	16	
FlexRay[1]	Optional feature	
FlexCAN (controller area network)	2[2,3]	
Safety port	Yes (via second FlexCAN module)	
FCU (fault collection unit)	Yes	
CTU (cross triggering unit)	Yes	



Legend:

ADC	Analog-to-digital converter
BAM	Boot assist module
CRC	Cyclic redundancy check
CTU	Cross triggering unit
DSPI	Deserial serial peripheral interface
ECSM	Error correction status module
eDMA	Enhanced direct memory access
eTimer	Enhanced timer
FCU	Fault collection unit
Flash	Flash memory
FlexCAN	Controller area network
FlexPWM	Flexible pulse width modulation
FMPLL	Frequency-modulated phase-locked loop
INTC	Interrupt controller
JTAG	JTAG controller
LINFlex	Serial communication interface (LIN support)
MC_CGM	Clock generation module
MC_ME	Mode entry module
MC_PCU	Power control unit
MC_RGM	Reset generation module
PIT	Periodic interrupt timer
SIUL	System integration unit Lite
SRAM	Static random-access memory
SSCM	System status and configuration module
STM	System timer module
SWT	Software watchdog timer
WKPU	Wakeup unit
XOSC	External oscillator
XBAR	Crossbar switch

Figure 1. MPC5604P block diagram

- 32 message buffers of up to 8-bytes data length
- Each message buffer configurable as Rx or Tx, all supporting standard and extended messages
- Programmable loop-back mode supporting self-test operation
- 3 programmable mask registers
- Programmable transmit-first scheme: lowest ID or lowest buffer number
- Time stamp based on 16-bit free-running timer
- Global network time, synchronized by a specific message
- Maskable interrupts
- Independent of the transmission medium (an external transceiver is assumed)
- High immunity to EMI
- Short latency time due to an arbitration scheme for high-priority messages
- Transmit features
  - Supports configuration of multiple mailboxes to form message queues of scalable depth
  - Arbitration scheme according to message ID or message buffer number
  - Internal arbitration to guarantee no inner or outer priority inversion
  - Transmit abort procedure and notification
- Receive features
  - Individual programmable filters for each mailbox
  - 8 mailboxes configurable as a six-entry receive FIFO
  - 8 programmable acceptance filters for receive FIFO
- Programmable clock source
  - System clock
  - Direct oscillator clock to avoid PLL jitter

1.5.21 Safety port (FlexCAN)

The MPC5604P MCU has a second CAN controller synthesized to run at high bit rates to be used as a safety port. The CAN module of the safety port provides the following features:

- Identical to the FlexCAN module
- Bit rate as fast as 7.5 Mbit/s at 60 MHz CPU clock using direct connection between CAN modules (no physical transceiver required)
- 32 message buffers of up to 8 bytes data length
- Can be used as a second independent CAN module

1.5.22 FlexRay

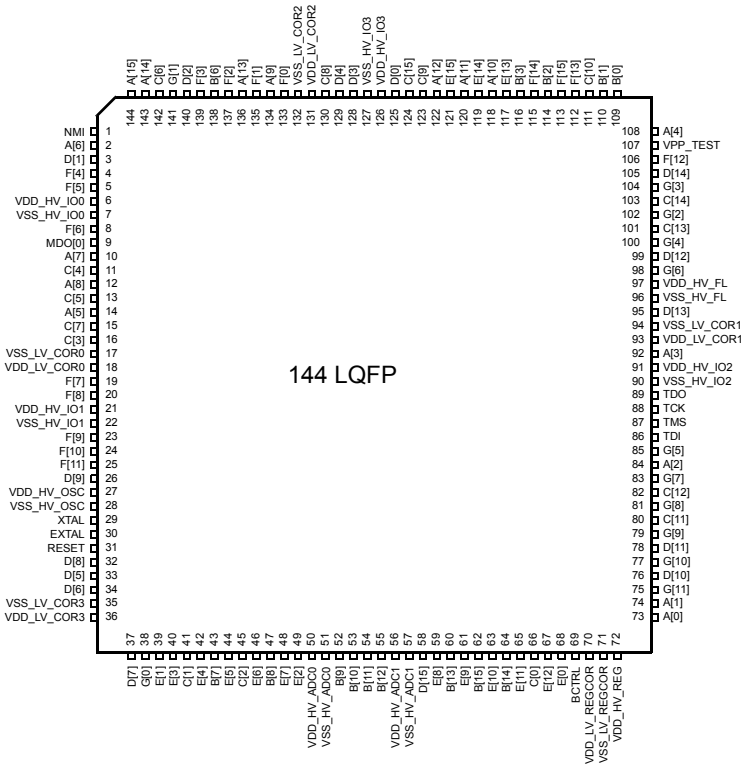
The FlexRay module provides the following features:

- Full implementation of FlexRay Protocol Specification 2.1
- 32 configurable message buffers can be handled
- Dual channel or single channel mode of operation, each as fast as 10 Mbit/s data rate
- Message buffers configurable as Tx, Rx or RxFIFO
- Message buffer size configurable
- Message filtering for all message buffers based on FrameID, cycle count and message ID
- Programmable acceptance filters for RxFIFO message buffers

2 Package pinouts and signal descriptions

2.1 Package pinouts

The LQFP pinouts are shown in the following figures.



Note: Availability of port pin alternate functions depends on product selection.

Figure 2. 144-pin LQFP pinout (top view)

Table 5. Pin muxing

Port pin	Pad configuration register (PCR)	Alternate function[1,2]	Functions	Peripheral[3]	I/O direction[4]	Pad speed[5]		Pin No.	
						SRC = 0	SRC = 1	100-pin	144-pin
Port A (16-bit)									
A[0]	PCR[0]	ALT0 ALT1 ALT2 ALT3 —	GPIO[0] ETC[0] SCK F[0] EIRQ[0]	SIUL eTimer_0 DSPI_2 FCU_0 SIUL	I/O I/O O O I	Slow	Medium	51	73
A[1]	PCR[1]	ALT0 ALT1 ALT2 ALT3 —	GPIO[1] ETC[1] SOUT F[1] EIRQ[1]	SIUL eTimer_0 DSPI_2 FCU_0 SIUL	I/O I/O O O I	Slow	Medium	52	74
A[2][6]	PCR[2]	ALT0 ALT1 ALT2 ALT3 — — —	GPIO[2] ETC[2] — A[3] SIN ABS[0] EIRQ[2]	SIUL eTimer_0 — FlexPWM_0 DSPI_2 MC_RGM SIUL	I/O I/O — O I I I	Slow	Medium	57	84
A[3][6]	PCR[3]	ALT0 ALT1 ALT2 ALT3 — —	GPIO[3] ETC[3] CS0 B[3] ABS[2] EIRQ[3]	SIUL eTimer_0 DSPI_2 FlexPWM_0 MC_RGM SIUL	I/O I/O I/O O I I	Slow	Medium	64	92
A[4][6]	PCR[4]	ALT0 ALT1 ALT2 ALT3 — —	GPIO[4] ETC[0] CS1 ETC[4] FAB EIRQ[4]	SIUL eTimer_1 DSPI_2 eTimer_0 MC_RGM SIUL	I/O I/O O I/O I I	Slow	Medium	75	108
A[5]	PCR[5]	ALT0 ALT1 ALT2 ALT3 —	GPIO[5] CS0 ETC[5] CS7 EIRQ[5]	SIUL DSPI_1 eTimer_1 DSPI_0 SIUL	I/O I/O I/O O I	Slow	Medium	8	14
A[6]	PCR[6]	ALT0 ALT1 ALT2 ALT3 —	GPIO[6] SCK — — EIRQ[6]	SIUL DSPI_1 — — SIUL	I/O I/O — — I	Slow	Medium	2	2
A[7]	PCR[7]	ALT0 ALT1 ALT2 ALT3 —	GPIO[7] SOUT — — EIRQ[7]	SIUL DSPI_1 — — SIUL	I/O O — — I	Slow	Medium	4	10

Table 5. Pin muxing (continued)

Port pin	Pad configuration register (PCR)	Alternate function[1,2]	Functions	Peripheral[3]	I/O direction[4]	Pad speed[5]		Pin No.	
						SRC = 0	SRC = 1	100-pin	144-pin
B[10]	PCR[26]	ALT0 ALT1 ALT2 ALT3 —	GPIO[26] — — — AN[12]	SIUL — — — ADC_0 / ADC_1	Input only	—	—	36	53
B[11]	PCR[27]	ALT0 ALT1 ALT2 ALT3 —	GPIO[27] — — — AN[13]	SIUL — — — ADC_0 / ADC_1	Input only	—	—	37	54
B[12]	PCR[28]	ALT0 ALT1 ALT2 ALT3 —	GPIO[28] — — — AN[14]	SIUL — — — ADC_0 / ADC_1	Input only	—	—	38	55
B[13]	PCR[29]	ALT0 ALT1 ALT2 ALT3 — —	GPIO[29] — — — AN[0] RXD	SIUL — — — ADC_1 LIN_1	Input only	—	—	42	60
B[14]	PCR[30]	ALT0 ALT1 ALT2 ALT3 — — —	GPIO[30] — — — AN[1] ETC[4] EIRQ[19]	SIUL — — — ADC_1 eTimer_0 SIUL	Input only	—	—	44	64
B[15]	PCR[31]	ALT0 ALT1 ALT2 ALT3 — —	GPIO[31] — — — AN[2] EIRQ[20]	SIUL — — — ADC_1 SIUL	Input only	—	—	43	62
Port C (16-bit)									
C[0]	PCR[32]	ALT0 ALT1 ALT2 ALT3 —	GPIO[32] — — — AN[3]	SIUL — — — ADC_1	Input only	—	—	45	66
C[1]	PCR[33]	ALT0 ALT1 ALT2 ALT3 —	GPIO[33] — — — AN[2]	SIUL — — — ADC_0	Input only	—	—	28	41

Table 5. Pin muxing (continued)

Port pin	Pad configuration register (PCR)	Alternate function[1,2]	Functions	Peripheral[3]	I/O direction[4]	Pad speed[5]		Pin No.	
						SRC = 0	SRC = 1	100-pin	144-pin
C[2]	PCR[34]	ALT0 ALT1 ALT2 ALT3 —	GPIO[34] — — — AN[3]	SIUL — — — ADC_0	Input only	—	—	30	45
C[3]	PCR[35]	ALT0 ALT1 ALT2 ALT3 —	GPIO[35] CS1 ETC[4] TXD EIRQ[21]	SIUL DSPI_0 eTimer_1 LIN_1 SIUL	I/O O I/O O I	Slow	Medium	10	16
C[4]	PCR[36]	ALT0 ALT1 ALT2 ALT3 —	GPIO[36] CS0 X[1] DEBUG[4] EIRQ[22]	SIUL DSPI_0 FlexPWM_0 SSCM SIUL	I/O I/O I/O — I	Slow	Medium	5	11
C[5]	PCR[37]	ALT0 ALT1 ALT2 ALT3 — —	GPIO[37] SCK — DEBUG[5] FAULT[3] EIRQ[23]	SIUL DSPI_0 — SSCM FlexPWM_0 SIUL	I/O I/O — — I I	Slow	Medium	7	13
C[6]	PCR[38]	ALT0 ALT1 ALT2 ALT3 —	GPIO[38] SOUT B[1] DEBUG[6] EIRQ[24]	SIUL DSPI_0 FlexPWM_0 SSCM SIUL	I/O I/O O — I	Slow	Medium	98	142
C[7]	PCR[39]	ALT0 ALT1 ALT2 ALT3 —	GPIO[39] — A[1] DEBUG[7] SIN	SIUL — FlexPWM_0 SSCM DSPI_0	I/O — O — I	Slow	Medium	9	15
C[8]	PCR[40]	ALT0 ALT1 ALT2 ALT3 —	GPIO[40] CS1 — CS6 FAULT[2]	SIUL DSPI_1 — DSPI_0 FlexPWM_0	I/O O — O I	Slow	Medium	91	130
C[9]	PCR[41]	ALT0 ALT1 ALT2 ALT3 —	GPIO[41] CS3 — X[3] FAULT[2]	SIUL DSPI_2 — FlexPWM_0 FlexPWM_0	I/O O — I/O I	Slow	Medium	84	123
C[10]	PCR[42]	ALT0 ALT1 ALT2 ALT3 —	GPIO[42] CS2 — A[3] FAULT[1]	SIUL DSPI_2 — FlexPWM_0 FlexPWM_0	I/O O — O I	Slow	Medium	78	111

Table 7. Absolute maximum ratings[1] (continued)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max[2]	
V_{INAN0}	SR	ADC0 and shared ADC0/1 analog input voltage[6]	$V_{DD\_HV\_REG}$ > 2.7 V	$V_{SS\_HV\_ADV0}$ – 0.3	$V_{DD\_HV\_ADV0}$ + 0.3	V
			$V_{DD\_HV\_REG}$ < 2.7 V	$V_{SS\_HV\_ADV0}$	$V_{DD\_HV\_ADV0}$	V
V_{INAN1}	SR	ADC1 analog input voltage[7]	$V_{DD\_HV\_REG}$ > 2.7 V	$V_{SS\_HV\_ADV1}$ – 0.3	$V_{DD\_HV\_ADV1}$ + 0.3	V
			$V_{DD\_HV\_REG}$ < 2.7 V	$V_{SS\_HV\_ADV1}$	$V_{DD\_HV\_ADV1}$	V
I_{INJPAD}	SR	Injected input current on any pin during overload condition	—	–10	10	mA
I_{INJSUM}	SR	Absolute sum of all injected input currents during overload condition	—	–50	50	mA
I_{VDD_LV}	SR	Low voltage static current sink through V_{DD_LV}	—	—	155	mA
T_{STG}	SR	Storage temperature	—	–55	150	°C
T_J	SR	Junction temperature under bias	—	–40	150	°C

1 Functional operating conditions are given in the DC electrical characteristics. Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the listed maxima may affect device reliability or cause permanent damage to the device.

2 Absolute maximum voltages are currently maximum burn-in voltages. Absolute maximum specifications for device stress have not yet been determined.

3 The difference between each couple of voltage supplies must be less than 300 mV, $|V_{DD\_HV\_IOy} - V_{DD\_HV\_IOx}| < 300$ mV.

4 The difference between ADC voltage supplies must be less than 100 mV, $|V_{DD\_HV\_ADC1} - V_{DD\_HV\_ADC0}| < 100$ mV.

5 Guaranteed by device validation

6 Not allowed to refer this voltage to $V_{DD\_HV\_ADV1}$, $V_{SS\_HV\_ADV1}$

7 Not allowed to refer this voltage to $V_{DD\_HV\_ADV0}$, $V_{SS\_HV\_ADV0}$

Figure 4 shows the constraints of the different power supplies.

3.4 Recommended operating conditions

Table 8. Recommended operating conditions (5.0 V)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max[1]	
V_{SS}	SR	Device ground	—	0	0	V
$V_{DD\_HV\_IOx}$[2]	SR	5.0 V input/output supply voltage	—	4.5	5.5	V
$V_{SS\_HV\_IOx}$	SR	Input/output ground voltage	—	0	0	V
$V_{DD\_HV\_FL}$	SR	5.0 V code and data flash supply voltage	—	4.5	5.5	V
			Relative to $V_{DD\_HV\_IOx}$	$V_{DD\_HV\_IOx}$ – 0.1	$V_{DD\_HV\_IOx}$ + 0.1	
$V_{SS\_HV\_FL}$	SR	Code and data flash ground	—	0	0	V
$V_{DD\_HV\_OSC}$	SR	5.0 V crystal oscillator amplifier supply voltage	—	4.5	5.5	V
			Relative to $V_{DD\_HV\_IOx}$	$V_{DD\_HV\_IOx}$ – 0.1	$V_{DD\_HV\_IOx}$ + 0.1	
$V_{SS\_HV\_OSC}$	SR	5.0 V crystal oscillator amplifier reference voltage	—	0	0	V
$V_{DD\_HV\_REG}$	SR	5.0 V voltage regulator supply voltage	—	4.5	5.5	V
			Relative to $V_{DD\_HV\_IOx}$	$V_{DD\_HV\_IOx}$ – 0.1	$V_{DD\_HV\_IOx}$ + 0.1	
$V_{DD\_HV\_ADC0}$[3]	SR	5.0 V ADC_0 supply and high reference voltage	—	4.5	5.5	V
			Relative to $V_{DD\_HV\_REG}$	$V_{DD\_HV\_REG}$ – 0.1	—	
$V_{SS\_HV\_ADC0}$	SR	ADC_0 ground and low reference voltage	—	0	0	V
$V_{DD\_HV\_ADC1}$[3]	SR	5.0 V ADC_1 supply and high reference voltage	—	4.5	5.5	V
			Relative to $V_{DD\_HV\_REG}$	$V_{DD\_HV\_REG}$ – 0.1	—	
$V_{SS\_HV\_ADC1}$	SR	ADC_1 ground and low reference voltage	—	0	0	V
$V_{DD\_LV\_REGCOR}$[4,5]	CC	Internal supply voltage	—	—	—	V
$V_{SS\_LV\_REGCOR}$[4]	SR	Internal reference voltage	—	0	0	V
$V_{DD\_LV\_CORx}$[4,5]	CC	Internal supply voltage	—	—	—	V
$V_{SS\_LV\_CORx}$[4]	SR	Internal reference voltage	—	0	0	V
T_A	SR	Ambient temperature under bias	—	–40	125	°C

1 Parametric figures can be out of specification when voltage drops below 4.5 V, however, guaranteeing the full functionality. In particular, ADC electrical characteristics and I/Os DC electrical specification may not be guaranteed.

2 The difference between each couple of voltage supplies must be less than 100 mV, $|V_{DD\_HV\_IOy} - V_{DD\_HV\_IOx}| < 100$ mV.

3 The difference between ADC voltage supplies must be less than 100 mV, $|V_{DD\_HV\_ADC1} - V_{DD\_HV\_ADC0}| < 100$ mV.

[5] Thermal characterization parameter indicating the temperature difference between the case and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JC.

3.5.2 General notes for specifications at maximum junction temperature

An estimation of the chip junction temperature, T_J, can be obtained from Equation 1:

$$T_J = T_A + (R_{\theta JA} * P_D) \quad \textit{Eqn. 1}$$

where:

T_A = ambient temperature for the package (°C)

$R_{\theta JA}$ = junction to ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

The junction to ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. Unfortunately, there are two values in common usage: the value determined on a single layer board and the value obtained on a board with two planes. For packages such as the PBGA, these values can be different by a factor of two. Which value is closer to the application depends on the power dissipated by other components on the board. The value obtained on a single layer board is appropriate for the tightly packed printed circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated.

When a heat sink is used, the thermal resistance is expressed in Equation 2 as the sum of a junction to case thermal resistance and a case to ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA} \quad \textit{Eqn. 2}$$

where:

$R_{\theta JA}$ = junction to ambient thermal resistance (°C/W)

$R_{\theta JC}$ = junction to case thermal resistance (°C/W)

$R_{\theta CA}$ = case to ambient thermal resistance (°C/W)

$R_{\theta JC}$ is device related and cannot be influenced by the user. The user controls the thermal environment to change the case to ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed circuit board, or change the thermal dissipation on the printed circuit board surrounding the device.

To determine the junction temperature of the device in the application when heat sinks are not used, the Thermal Characterization Parameter (Ψ_{JT}) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using Equation 3:

$$T_J = T_T + (\Psi_{JT} \times P_D) \quad \textit{Eqn. 3}$$

where:

T_T = thermocouple temperature on top of the package (°C)

Ψ_{JT} = thermal characterization parameter (°C/W)

P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

References:

3.8 Power management electrical characteristics

3.8.1 Voltage regulator electrical characteristics

The internal voltage regulator requires an external NPN ballast to be connected as shown in Figure 8. Table 14 contains all approved NPN ballast components. Capacitances should be placed on the board as near as possible to the associated pins. Care should also be taken to limit the serial inductance of the $V_{DD\_HV\_REG}$, BCTRL and $V_{DD\_LV\_CORx}$ pins to less than L_{Reg}, see Table 15.

NOTE

The voltage regulator output cannot be used to drive external circuits. Output pins are used only for decoupling capacitances.

$V_{DD\_LV\_COR}$ must be generated using internal regulator and external NPN transistor. It is not possible to provide $V_{DD\_LV\_COR}$ through external regulator.

For the MPC5604P microcontroller, capacitors, with total values not below C_{DEC1}, should be placed between $V_{DD\_LV\_CORx}/V_{SS\_LV\_CORx}$ close to external ballast transistor emitter. 4 capacitors, with total values not below C_{DEC2}, should be placed close to microcontroller pins between each $V_{DD\_LV\_CORx}/V_{SS\_LV\_CORx}$ supply pairs and the $V_{DD\_LV\_REGCOR}/V_{SS\_LV\_REGCOR}$ pair . Additionally, capacitors with total values not below C_{DEC3}, should be placed between the $V_{DD\_HV\_REG}/V_{SS\_HV\_REG}$ pins close to ballast collector. Capacitors values have to take into account capacitor accuracy, aging and variation versus temperature.

All reported information are valid for voltage and temperature ranges described in recommended operating condition, Table 8 and Table 9.

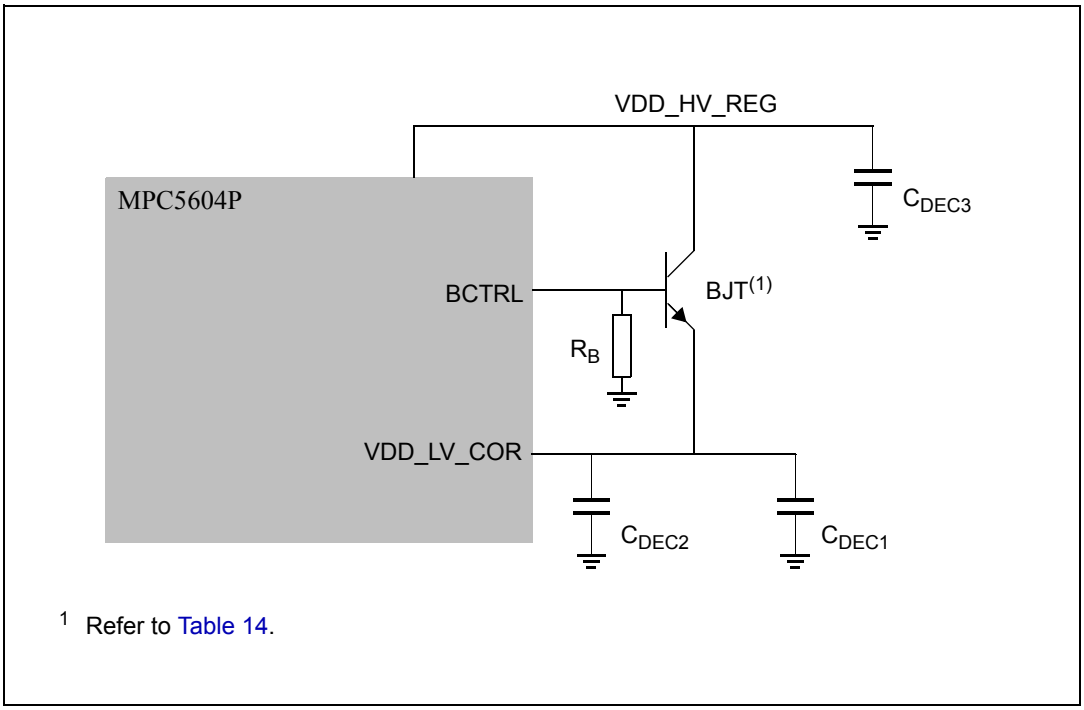


Figure 8. Configuration with resistor on base

Table 14. Approved NPN ballast components (configuration with resistor on base)

Part	Manufacturer	Approved derivatives[1]
BCP68	ON Semi	BCP68
	NXP	BCP68-25
	Infineon	BCP68-25
BCX68	Infineon	BCX68-10;BCX68-16;BCX68-25
BC868	NXP	BC868
BC817	Infineon	BC817-16;BC817-25;BC817SU;
	NXP	BC817-16;BC817-25
BCP56	ST	BCP56-16
	Infineon	BCP56-10;BCP56-16
	ON Semi	BCP56-10
	NXP	BCP56-10;BCP56-16

1 For automotive applications please check with the appropriate transistor vendor for automotive grade certification

Table 15. Voltage regulator electrical characteristics (configuration with resistor on base)

Symbol		C	Parameter	Conditions	Value			Unit
					Min	Typ	Max	
$V_{DD\_LV\_REGCOR}$	CC	P	Output voltage under maximum load run supply current configuration	Post-trimming	1.15	—	1.32	V
R_B	SR	—	External resistance on bipolar junction transistor (BJT) base	—	18	—	22	kΩ
C_{DEC1}	SR	—	External decoupling/stability ceramic capacitor	BJT from Table 14. 3 capacitances (i.e. X7R or X8R capacitors) with nominal value of 10 µF	19.5	30	—	µF
				BJT BC817, one capacitance of 22 µF	14.3	22		µF

[2] "SR" parameter values must not exceed the absolute maximum ratings shown in Table 7.

Table 22. Supply current (3.3 V, NVUSRO[PAD3V5V] = 1)

Symbol	C	Parameter		Conditions		Value		Unit
						Typ	Max	
$I_{DD\_LV\_CORx}$	T	Supply current	RUN—Maximum mode[1]	$V_{DD\_LV\_CORx}$ externally forced at 1.3 V	40 MHz	62	77	mA
					64 MHz	71	89	
			RUN—Typical mode[2]		40 MHz	45	56	
					64 MHz	53	66	
	P		RUN—Maximum mode[3]	$V_{DD\_LV\_CORx}$ externally forced at 1.3 V	64 MHz	60	75	
			HALT mode[4]	$V_{DD\_LV\_CORx}$ externally forced at 1.3 V	—	1.5	10	
			STOP mode[5]	$V_{DD\_LV\_CORx}$ externally forced at 1.3 V	—	1	10	
I_{DD_FLASH}	T		Flash during read on single mode	$V_{DD\_HV\_FL}$ at 3.3 V	—	8	10	
			Flash during erase operation on single mode	$V_{DD\_HV\_FL}$ at 3.3 V	—	10	12	
I_{DD_ADC}	T		ADC—Maximum mode[1]	$V_{DD\_HV\_ADC0}$ at 3.3 V $V_{DD\_HV\_ADC1}$ at 3.3 V f_{ADC} = 16 MHz	ADC_1	2.5	4	
					ADC_0	2	4	
			ADC—Typical mode[2]		ADC_1	0.8	1	
					ADC_0	0.005	0.006	
I_{DD_OSC}	T		Oscillator	V_{DD_OSC} at 3.3 V	8 MHz	2.4	3	

[1] Maximum mode: FlexPWM, ADCs, CTU, DSPI, LINFlex, FlexCAN, 15 output pins, 1st and 2nd PLL enabled. I/O supply current excluded.

[2] Typical mode: DSPI, LINFlex, FlexCAN, 15 output pins, 1st PLL only. I/O supply current excluded.

[3] Code fetched from RAM, PLL_0: 64 MHz system clock (x4 multiplier with 16 MHz XTAL), PLL_1 is ON at PHI_div2 = 120 MHz and PHI_div3 = 80 MHz, auxiliary clock sources set that all peripherals receive maximum frequency, all peripherals enabled.

[4] Halt mode configurations: code fetched from RAM, code and data flash memories in low power mode, OSC/PLL_0/PLL_1 are OFF, core clock frozen, all peripherals are disabled.

[5] STOP "P" mode Device Under Test (DUT) configuration: code fetched from RAM, code and data flash memories OFF, OSC/PLL_0/PLL_1 are OFF, core clock frozen, all peripherals are disabled.

3.10.4 Input DC electrical characteristics definition

Figure 13 shows the DC electrical characteristics behavior as function of time.

Table 24. I/O weight (continued)

Pad	144 LQFP		100 LQFP	
	Weight 5V	Weight 3.3V	Weight 5V	Weight 3.3V
PAD[27]	1%	1%	1%	1%
PAD[28]	1%	1%	1%	1%
PAD[63]	1%	1%	1%	1%
PAD[72]	1%	1%	—	—
PAD[29]	1%	1%	1%	1%
PAD[73]	1%	1%	—	—
PAD[31]	1%	1%	1%	1%
PAD[74]	1%	1%	—	—
PAD[30]	1%	1%	1%	1%
PAD[75]	1%	1%	—	—
PAD[32]	1%	1%	1%	1%
PAD[76]	1%	1%	—	—
PAD[64]	1%	1%	1%	1%
PAD[0]	23%	20%	23%	20%
PAD[1]	21%	18%	21%	18%
PAD[107]	20%	17%	—	—
PAD[58]	19%	16%	19%	16%
PAD[106]	18%	16%	—	—
PAD[59]	17%	15%	17%	15%
PAD[105]	16%	14%	—	—
PAD[43]	15%	13%	15%	13%
PAD[104]	14%	13%	—	—
PAD[44]	13%	12%	13%	12%
PAD[103]	12%	11%	—	—
PAD[2]	11%	10%	11%	10%
PAD[101]	11%	9%	—	—
PAD[21]	10%	8%	10%	8%
TMS	1%	1%	1%	1%
TCK	1%	1%	1%	1%
PAD[20]	16%	11%	16%	11%
PAD[3]	4%	3%	4%	3%
PAD[61]	9%	8%	9%	8%
PAD[102]	11%	10%	—	—

Table 27. Main oscillator output electrical characteristics (3.3 V, NVUSRO[PAD3V5V] = 1)

Symbol		C	Parameter	Value		Unit
				Min	Max	
f_{OSC}	S R	—	Oscillator frequency	4	40	MHz
g_m	—	P	Transconductance	4	20	mA/V
V_{OSC}	—	T	Oscillation amplitude on XTAL pin	1	—	V
t_{OSCSU}	—	T	Start-up time[1,2]	8	—	ms

1 The start-up time is dependent upon crystal characteristics, board leakage, etc., high ESR and excessive capacitive loads can cause long start-up time.

2 Value captured when amplitude reaches 90% of XTAL

Table 28. Input clock characteristics

Symbol		Parameter	Value			Unit
			Min	Typ	Max	
f_{OSC}	SR	Oscillator frequency	4	—	40	MHz
f_{CLK}	SR	Frequency in bypass	—	—	64	MHz
t_{rCLK}	SR	Rise/fall time in bypass	—	—	1	ns
t_{DC}	SR	Duty cycle	47.5	50	52.5	%

3.12 FMPLL electrical characteristics

Table 29. FMPLL electrical characteristics

Symbol	C	Parameter	Conditions[1]	Value		Unit
				Min	Max	
$f_{ref\_crystal}$ f_{ref_ext}	D	PLL reference frequency range[2]	Crystal reference	4	40	MHz
f_{PLLIN}	D	Phase detector input frequency range (after pre-divider)	—	4	16	MHz
$f_{FMPLLOUT}$	D	Clock frequency range in normal mode	—	16	120	MHz
f_{FREE}	P	Free-running frequency	Measured using clock division — typically /16	20	150	MHz
t_{CYC}	D	System clock period	—	—	1 / f_{SYS}	ns
f_{LORL} f_{LORH}	D	Loss of reference frequency window[3]	Lower limit	1.6	3.7	MHz
			Upper limit	24	56	
f_{SCM}	D	Self-clocked mode frequency[4,5]	—	20	150	MHz

Table 29. FMPLL electrical characteristics (continued)

Symbol	C	Parameter		Conditions[1]	Value		Unit
					Min	Max	
C_{JITTER}	T	CLKOUT period jitter[6,7,8,9]	Short-term jitter[10]	f_{SYS} maximum	–4	4	% f_{CLKOUT}
			Long-term jitter (avg. over 2 ms interval)	f_{PLLIN} = 16 MHz (resonator), f_{PLLCLK} at 64 MHz, 4,000 cycles	—	10	ns
t_{lpll}	D	PLL lock time [11, 12]		—	—	200	µs
t_{dc}	D	Duty cycle of reference		—	40	60	%
f_{LCK}	D	Frequency LOCK range		—	–6	6	% f_{SYS}
f_{UL}	D	Frequency un-LOCK range		—	-18	18	% f_{SYS}
f_{CS} f_{DS}	D	Modulation depth		Center spread	±0.25	±4.0[13]	% f_{SYS}
				Down spread	–0.5	–8.0	
f_{MOD}	D	Modulation frequency[14]		—	—	70	kHz

1 $V_{DD\_LV\_CORx}$ = 1.2 V ±10%; V_{SS} = 0 V; T_A = –40 to 125 °C, unless otherwise specified

2 Considering operation with PLL not bypassed

3 “Loss of Reference Frequency” window is the reference frequency range outside of which the PLL is in self-clocked mode.

4 Self-clocked mode frequency is the frequency that the PLL operates at when the reference frequency falls outside the f_{LOR} window.

5 f_{VCO} self clock range is 20–150 MHz. f_{SCM} represents f_{SYS} after PLL output divider (ERFD) of 2 through 16 in enhanced mode.

6 This value is determined by the crystal manufacturer and board design.

7 Jitter is the average deviation from the programmed frequency measured over the specified interval at maximum f_{SYS}. Measurements are made with the device powered by filtered supplies and clocked by a stable external clock signal. Noise injected into the PLL circuitry via V_{DDPLL} and V_{SSPLL} and variation in crystal oscillator frequency increase the C_{JITTER} percentage for a given interval.

8 Proper PC board layout procedures must be followed to achieve specifications.

9 Values are with frequency modulation disabled. If frequency modulation is enabled, jitter is the sum of C_{JITTER} and either f_{CS} or f_{DS} (depending on whether center spread or down spread modulation is enabled).

10 Short term jitter is measured on the clock rising edge at cycle n and cycle n+4.

11 This value is determined by the crystal manufacturer and board design. For 4 MHz to 20 MHz crystals specified for this PLL, load capacitors should not exceed these limits.

12 This specification applies to the period required for the PLL to relock after changing the MFD frequency control bits in the synthesizer control register (SYNCR).

13 This value is true when operating at frequencies above 60 MHz, otherwise f_{CS} is 2% (above 64 MHz).

14 Modulation depth will be attenuated from depth setting when operating at modulation frequencies above 50 kHz.

Table 34. Flash memory read access timing

Symbol	C	Parameter	Conditions[1]	Max value	Unit
f_{max}	C	Maximum working frequency at given number of wait states in worst conditions	2 wait states	66	MHz
			0 wait states	18	

[1] V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

3.16 AC specifications

3.16.1 Pad AC specifications

Table 35. Output pin transition times

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
t_{tr}	CC	D	Output transition time output pin[2] SLOW configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	50	ns
		T		C_L = 50 pF		—	—	100	
		D		C_L = 100 pF		—	—	125	
		D		C_L = 25 pF	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	40	
		T		C_L = 50 pF		—	—	50	
		D		C_L = 100 pF		—	—	75	
t_{tr}	CC	D	Output transition time output pin[2] MEDIUM configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 SIUL.PCRx.SRC = 1	—	—	10	ns
		T		C_L = 50 pF		—	—	20	
		D		C_L = 100 pF		—	—	40	
		D		C_L = 25 pF	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 SIUL.PCRx.SRC = 1	—	—	12	
		T		C_L = 50 pF		—	—	25	
		D		C_L = 100 pF		—	—	40	
t_{tr}	CC	D	Output transition time output pin[2] FAST configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 SIUL.PCRx.SRC = 1	—	—	4	ns
				C_L = 50 pF		—	—	6	
				C_L = 100 pF		—	—	12	
				C_L = 25 pF	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 SIUL.PCRx.SRC = 1	—	—	4	
				C_L = 50 pF		—	—	7	
				C_L = 100 pF		—	—	12	
t_{SYM}[3]	CC	T	Symmetric transition time, same drive strength between N and P transistor	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0		—	—	4	ns
				V_{DD} = 3.3 V ± 10%, PAD3V5V = 1		—	—	5	

[1] V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 °C to $T_{A\ MAX}$, unless otherwise specified

[2] C_L includes device and package capacitances (C_{PKG} < 5 pF).

[3] Transition timing of both positive and negative slopes will differ maximum 50%

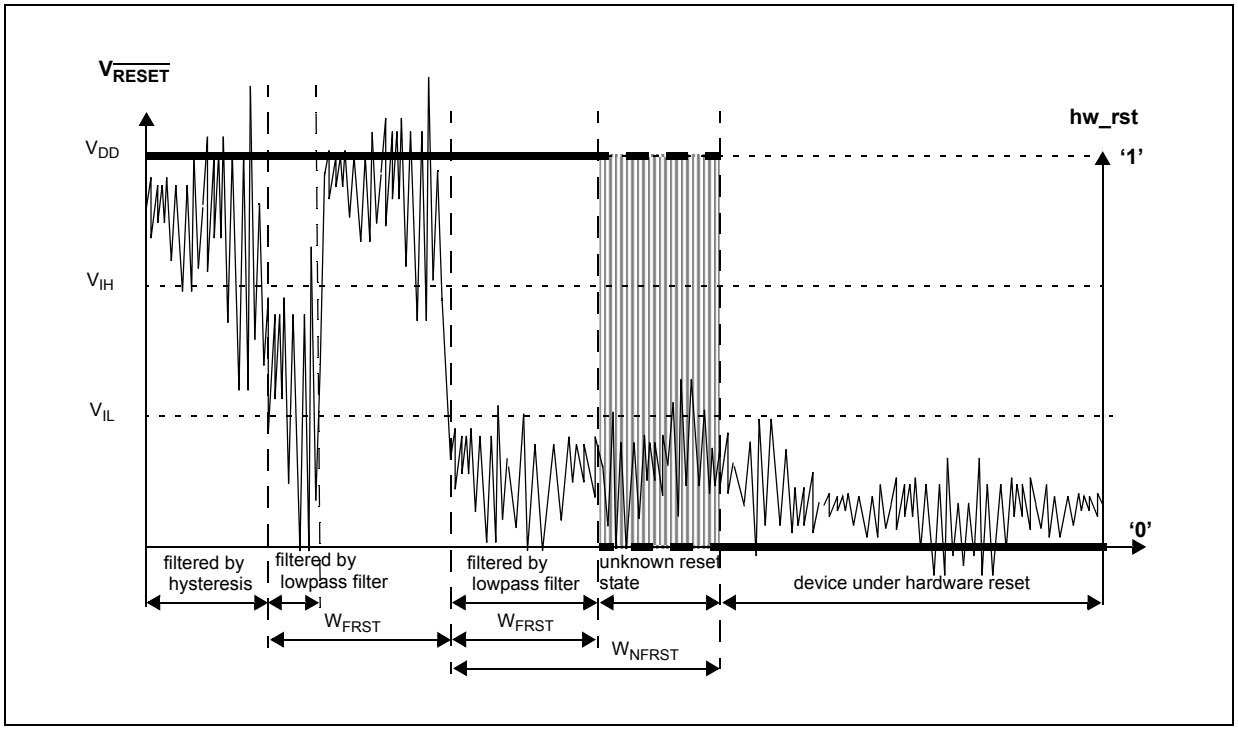
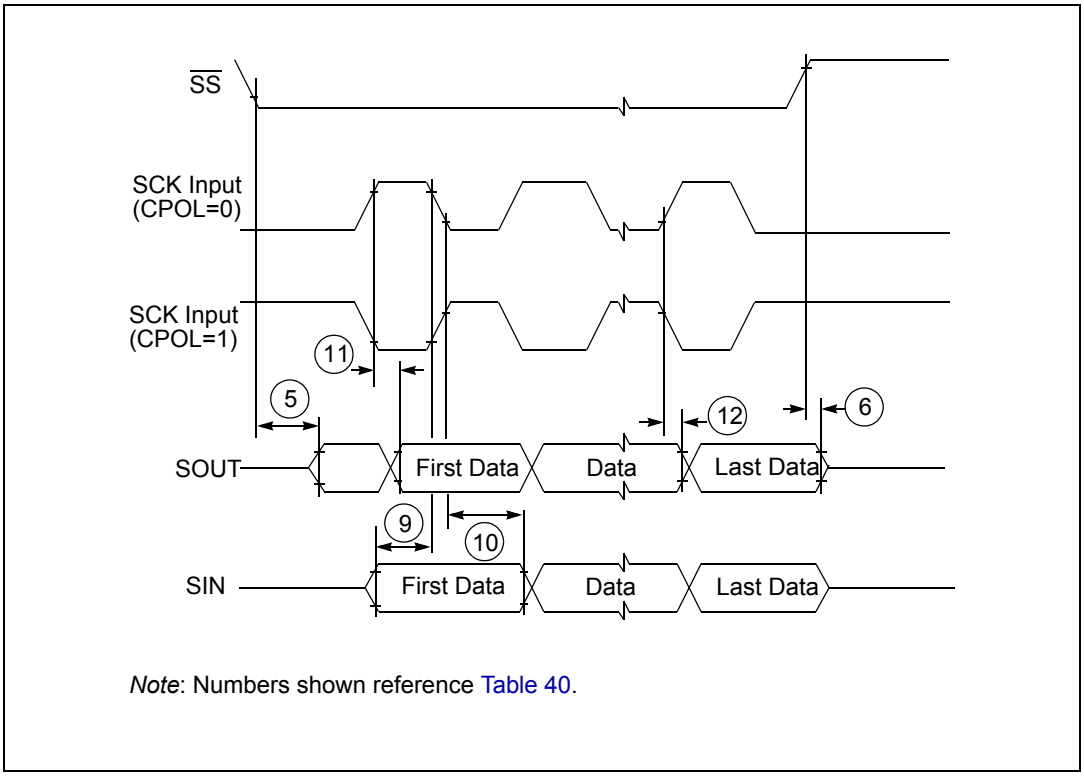


Figure 20. Noise filtering on reset signal

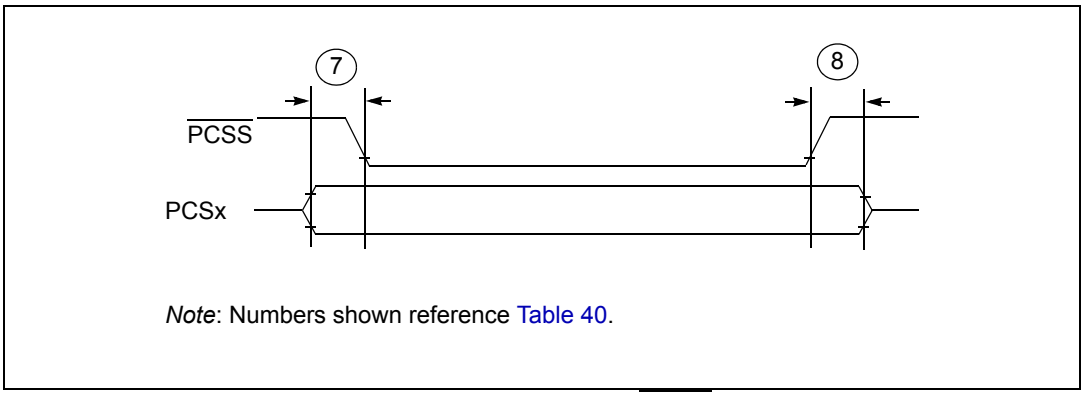
Table 36. $\overline{\text{RESET}}$ electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
V_{IH}	SR	P	Input High Level CMOS (Schmitt Trigger)	—	$0.65V_{DD}$	—	$V_{DD}+0.4$	V
V_{IL}	SR	P	Input low Level CMOS (Schmitt Trigger)	—	–0.4	—	$0.35V_{DD}$	V
V_{HYS}	CC	C	Input hysteresis CMOS (Schmitt Trigger)	—	$0.1V_{DD}$	—	—	V
V_{OL}	CC	P	Output low level	Push Pull, I_{OL} = 2mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	—	—	$0.1V_{DD}$	V
				Push Pull, I_{OL} = 1mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[2]	—	—	$0.1V_{DD}$	
				Push Pull, I_{OL} = 1mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	—	—	0.5	



Note: Numbers shown reference Table 40.

Figure 35. DSPI modified transfer format timing – Slave, CPHA = 1



Note: Numbers shown reference Table 40.

Figure 36. DSPI PCS strobe (PCSS) timing

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